

Fig. 1

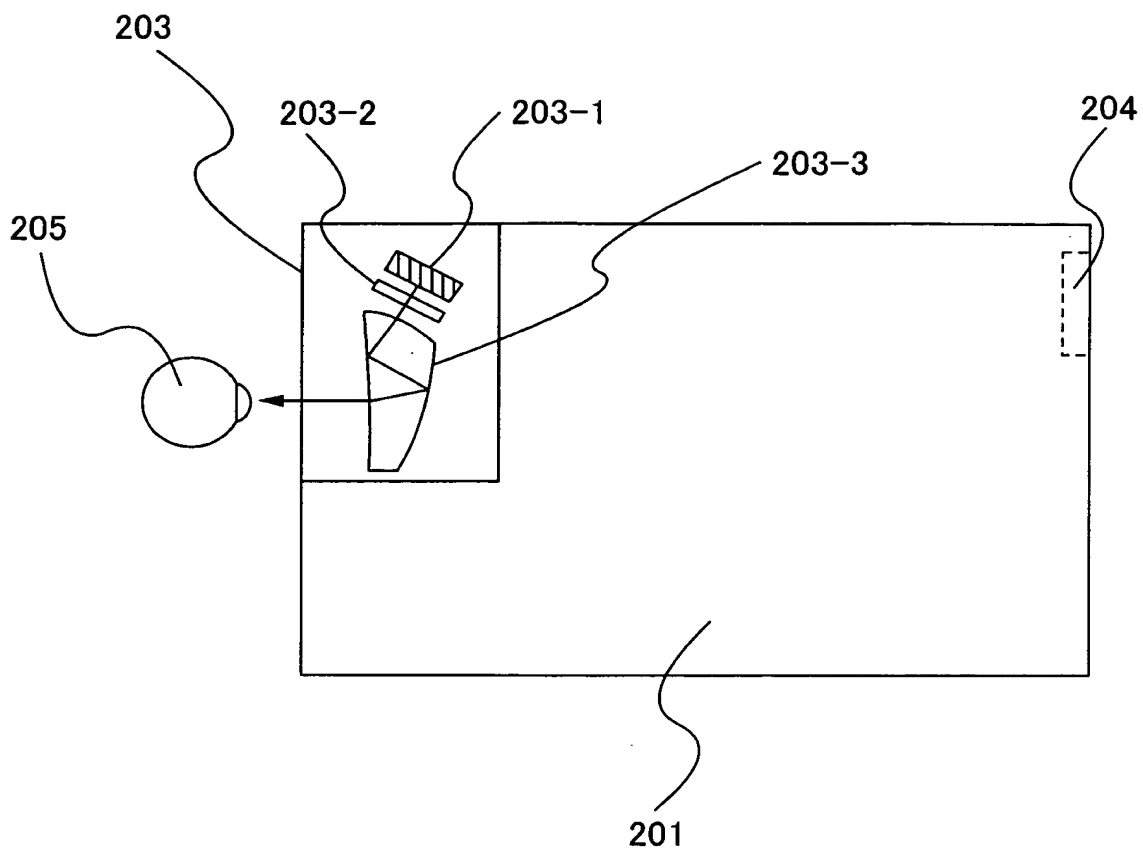
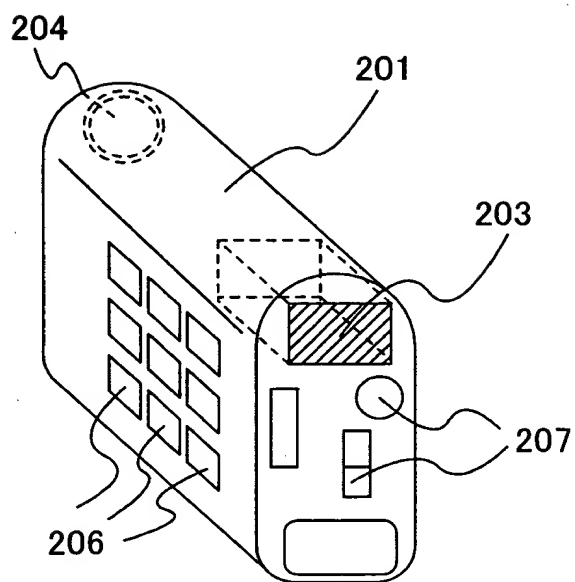
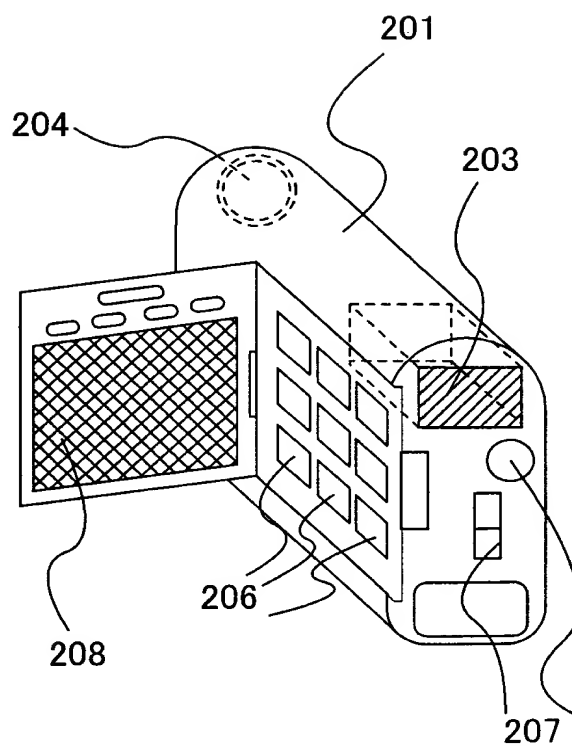


Fig. 2



**Fig. 3A**



**Fig. 3B.**

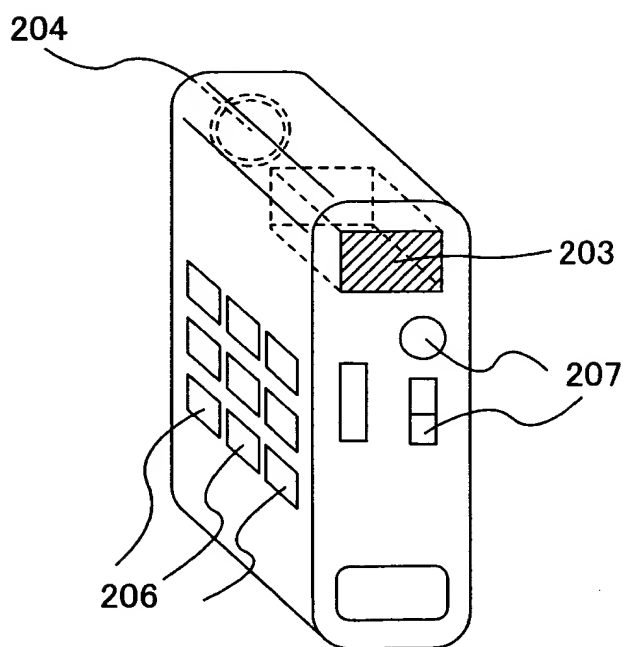


Fig. 3C

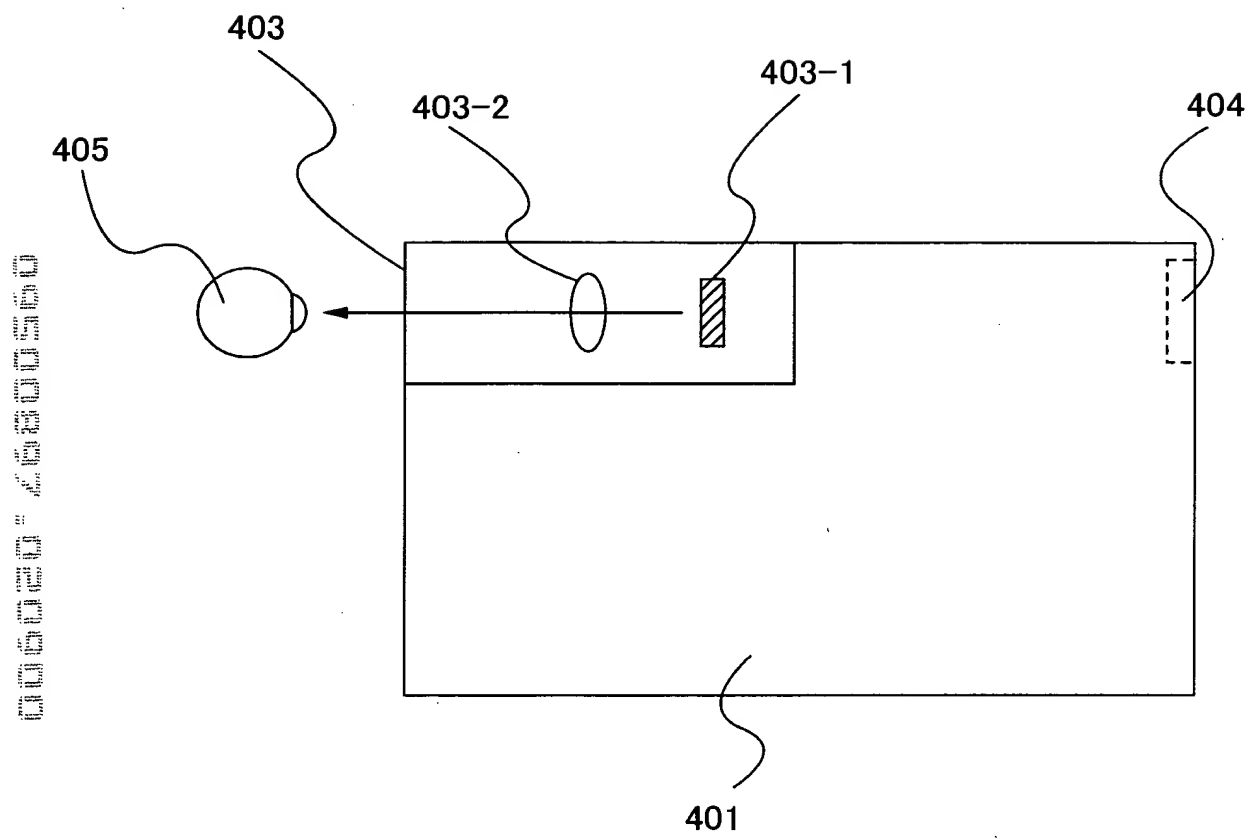


Fig. 4





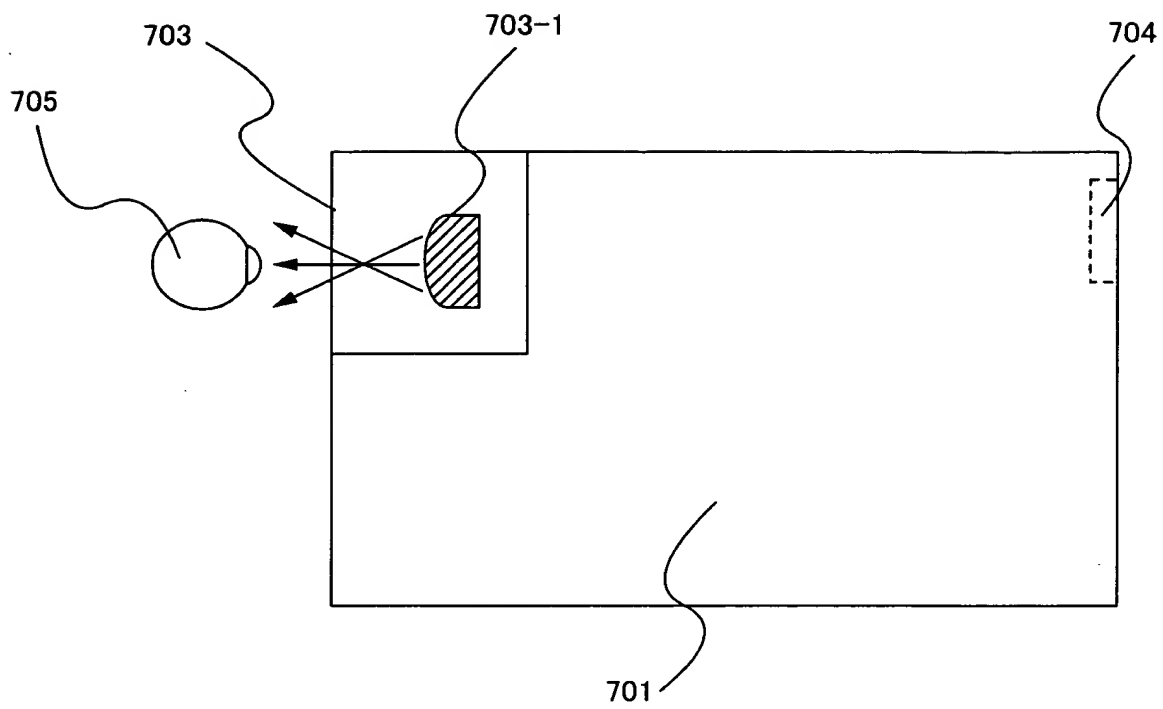


Fig. 7A

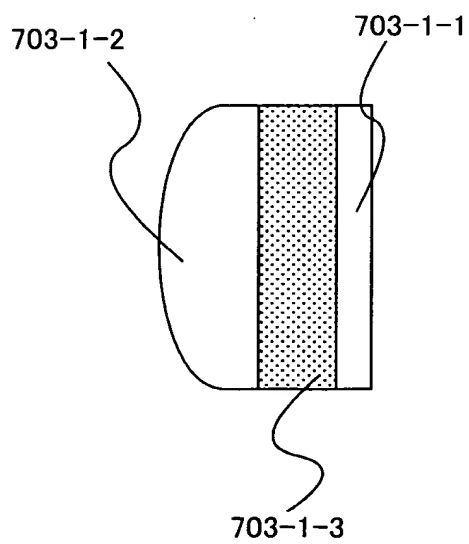


Fig. 7B

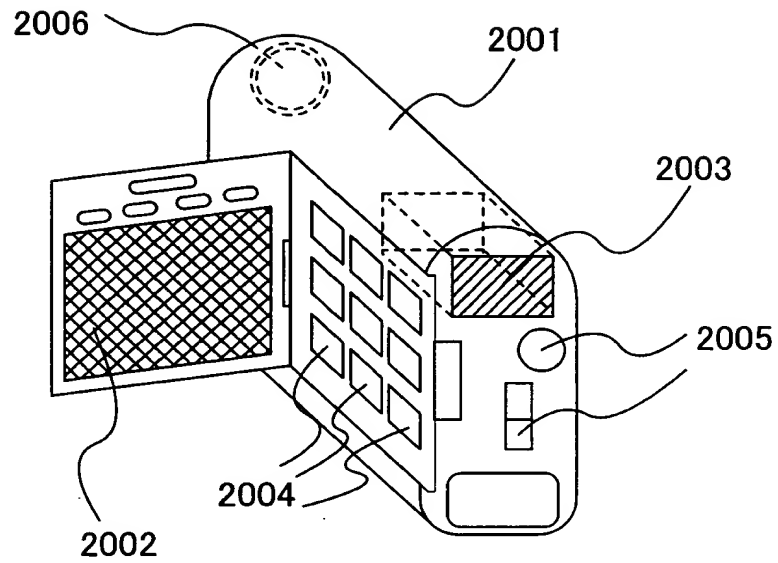


Fig. 8A (PRIOR ART)

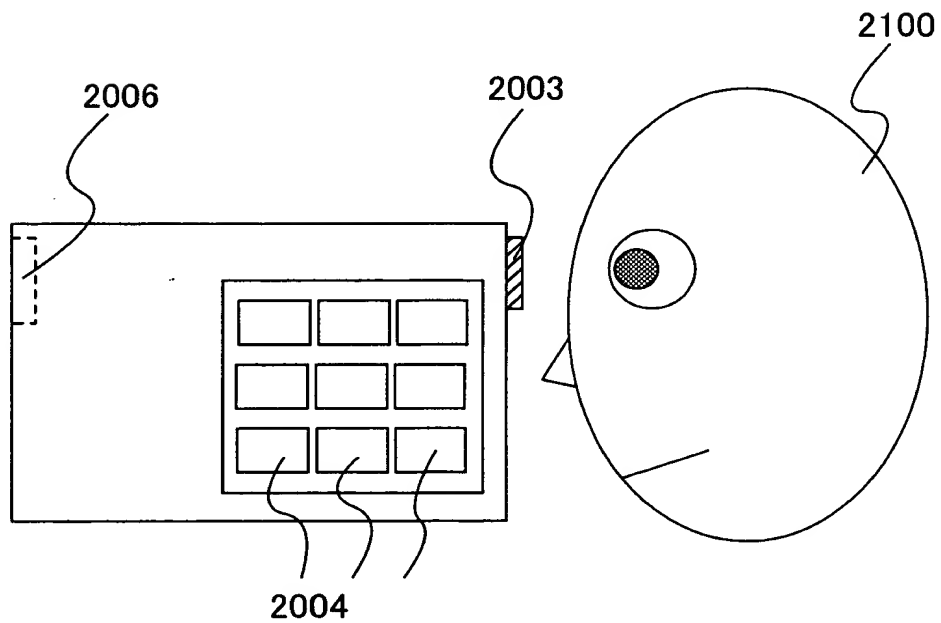


Fig. 8B (PRIOR ART)



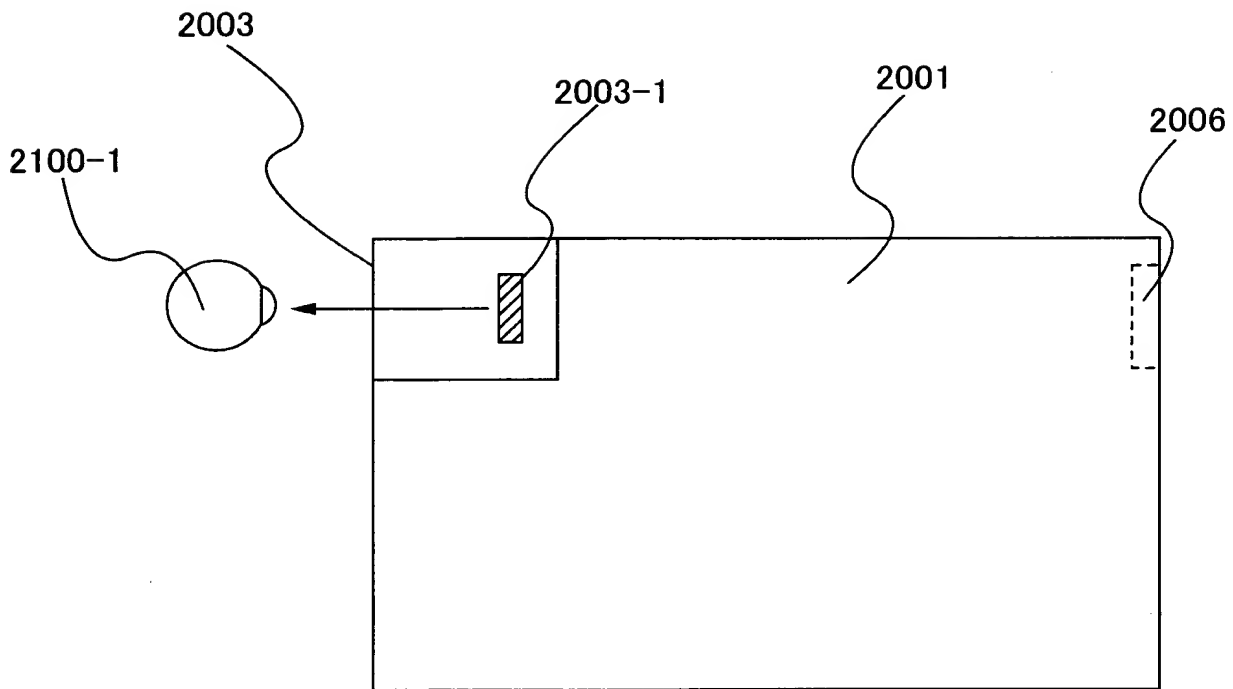


Fig. 9  
(PRIOR ART)

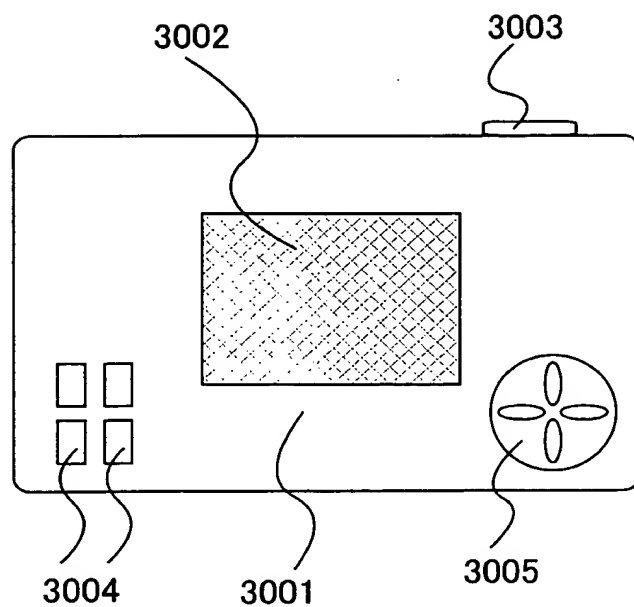


Fig. 10 (PRIOR ART)

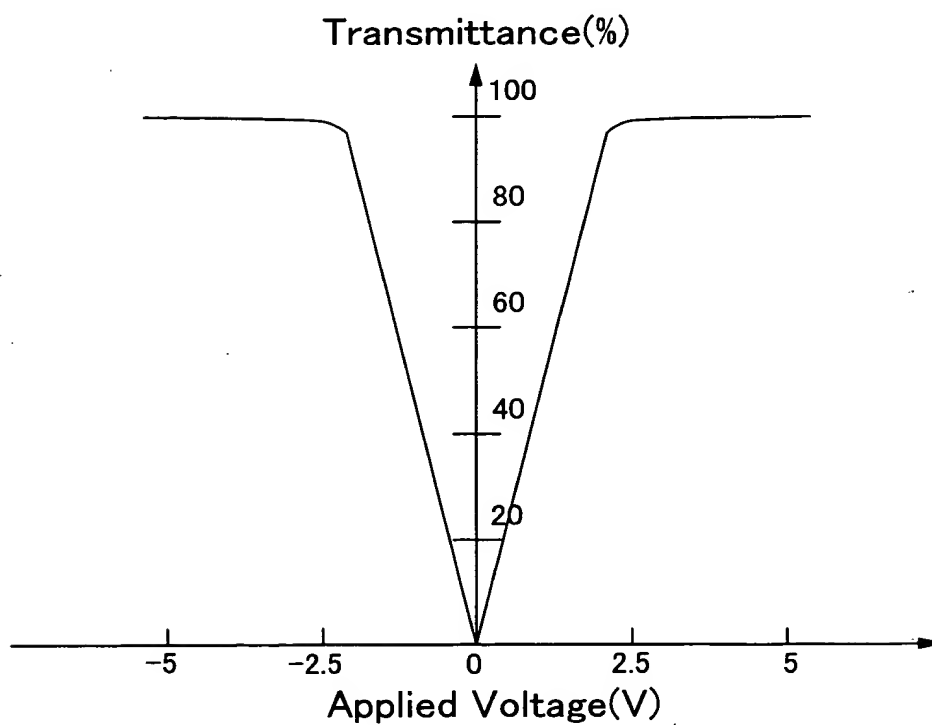
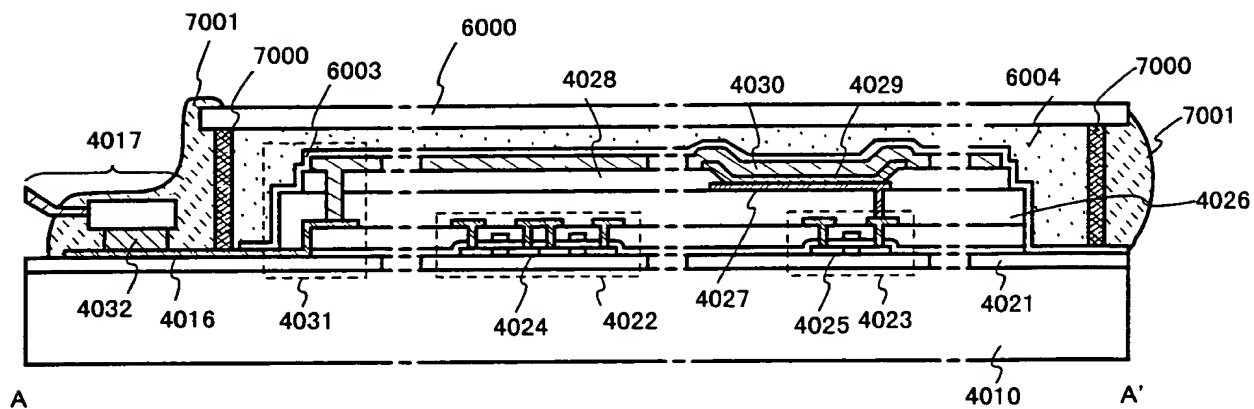
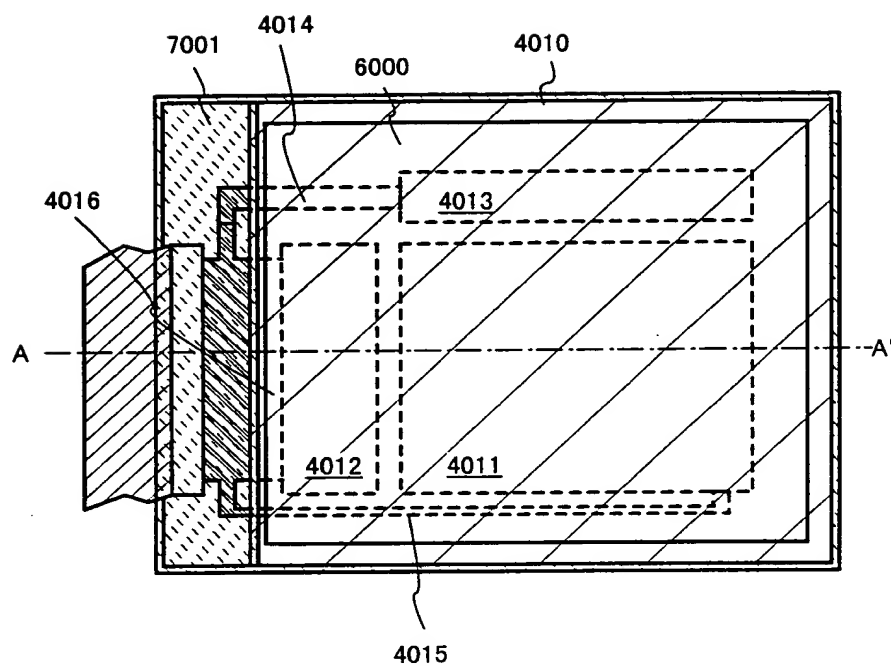


Fig. 11



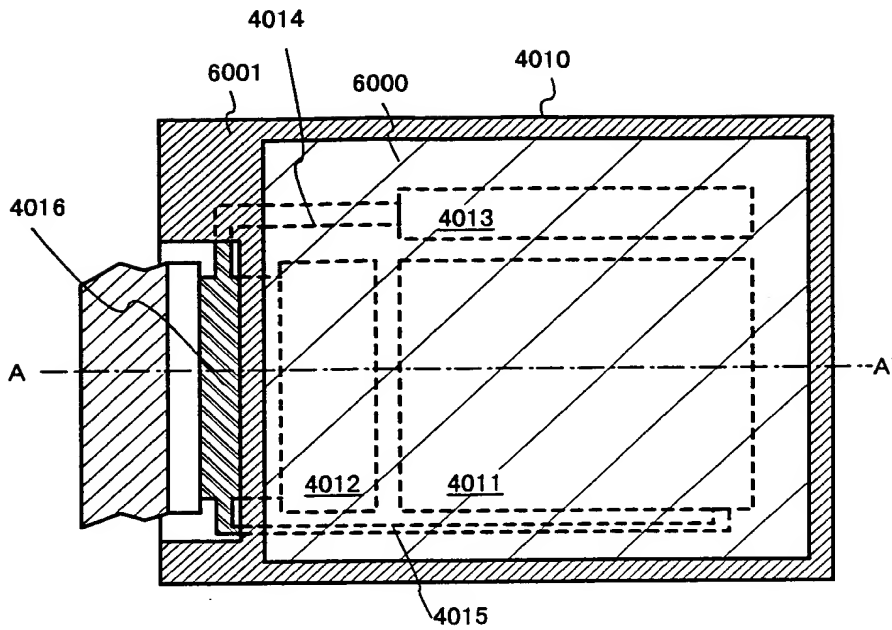


Fig. 13A

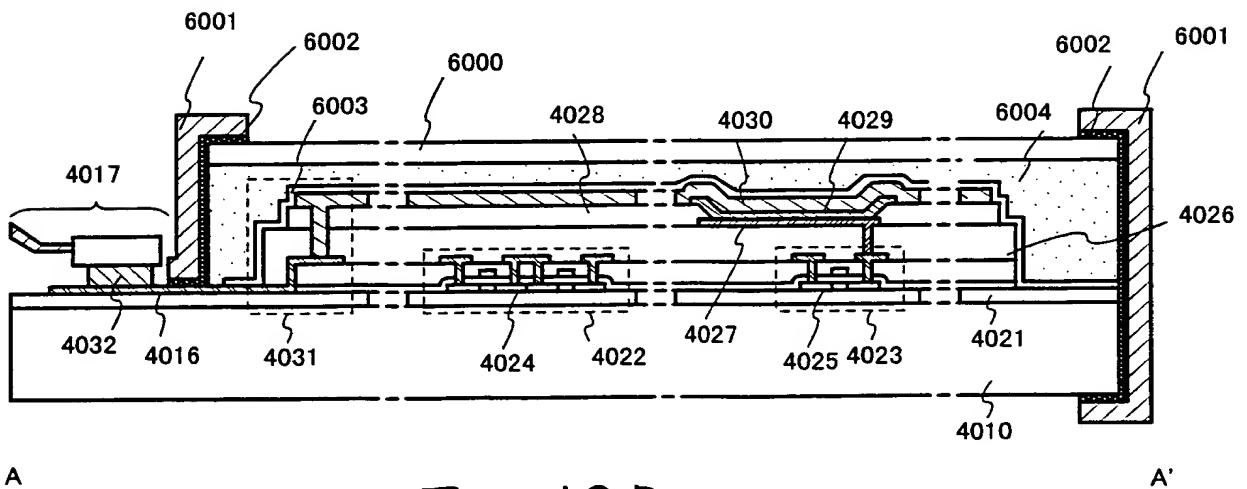


Fig. 13B

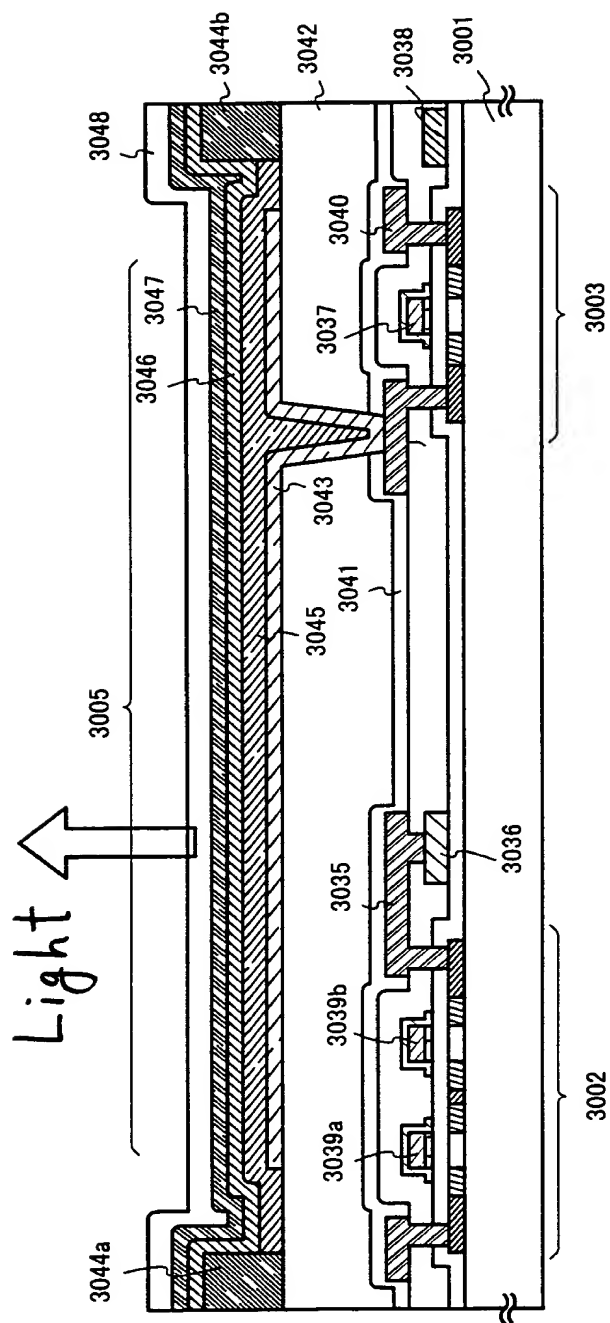


Fig. 14

This cross-sectional view shows a semiconductor device with a trench 3043. A gate structure 3004 is formed on the top surface of the device. The gate structure includes a gate oxide layer 3035 and a gate electrode 3036. The gate electrode is divided into two parts, 3039a and 3039b, which are separated by a gap 3040. The gate structure is formed on a substrate 3044a and 3044b. The trench 3043 is formed in the substrate. The gate structure 3004 is formed on the top surface of the device. The gate oxide layer 3035 is formed on the top surface of the device. The gate electrode 3036 is formed on the top surface of the device. The gate electrode is divided into two parts, 3039a and 3039b, which are separated by a gap 3040. The gate structure is formed on a substrate 3044a and 3044b. The trench 3043 is formed in the substrate. The gate structure 3004 is formed on the top surface of the device. The gate oxide layer 3035 is formed on the top surface of the device. The gate electrode 3036 is formed on the top surface of the device. The gate electrode is divided into two parts, 3039a and 3039b, which are separated by a gap 3040. The gate structure is formed on a substrate 3044a and 3044b. The trench 3043 is formed in the substrate.

Fig. 15A

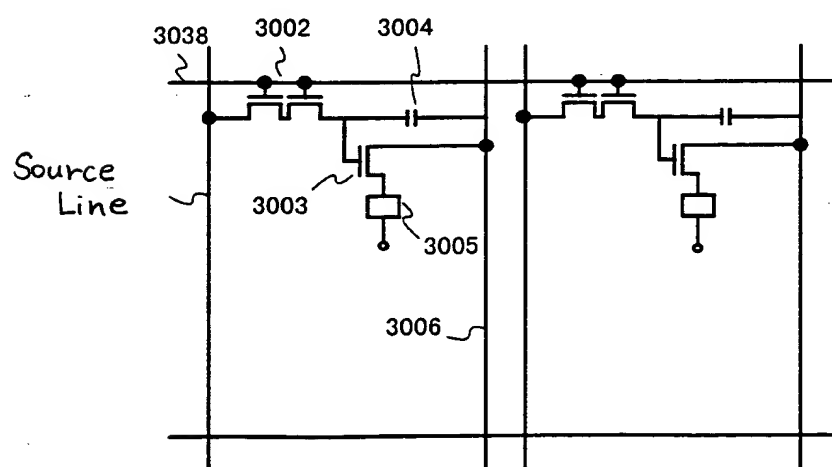


Fig. 15B

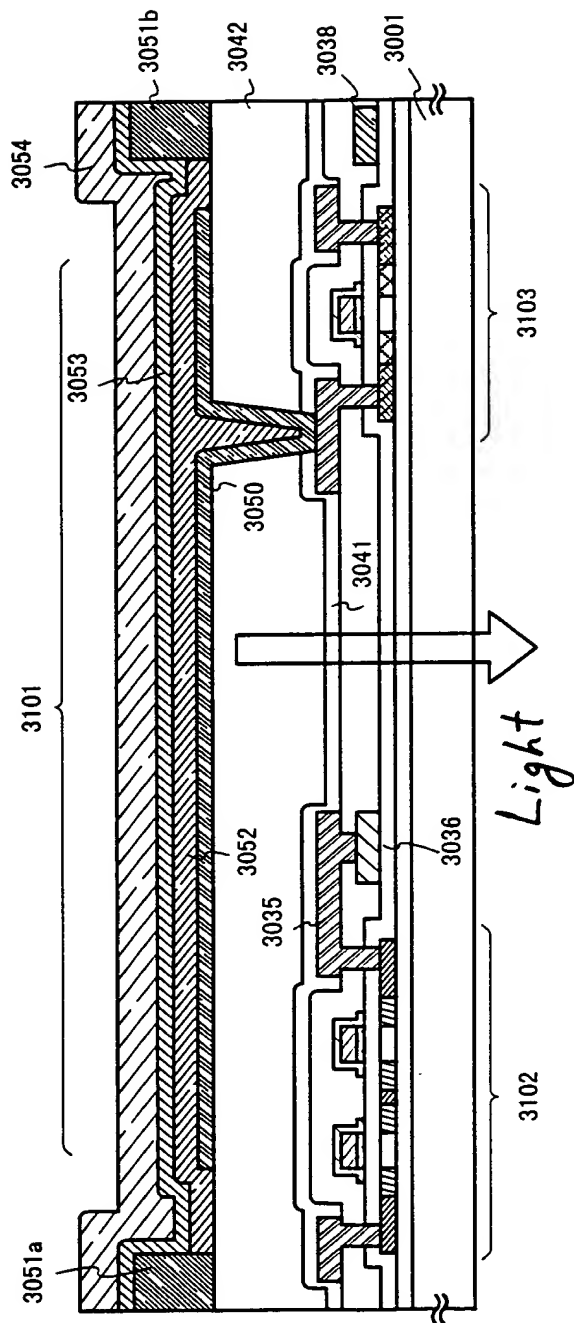


Fig. 16

